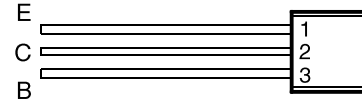




TIPP115, TIPP116, TIPP117 PNP SILICON POWER DARLINGTONS

- 20 W Pulsed Power Dissipation
- 100 V Capability
- 2 A Continuous Collector Current
- 4 A Peak Collector Current

LP PACKAGE
(TOP VIEW)



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIPP115	V_{CBO}	-60	V
	TIPP116		-80	
	TIPP117		-100	
Collector-emitter voltage ($I_B = 0$)	TIPP115	V_{CEO}	-60	V
	TIPP116		-80	
	TIPP117		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-2	A
Peak collector current (see Note 1)		I_{CM}	-4	A
Continuous base current		I_B	-50	mA
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	0.8	W
Pulsed power dissipation (see Note 3)		P_T	20	W
Operating junction temperature range		T_J	-55 to +150	°C
Storage temperature range		T_{stg}	-55 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
2. Derate linearly to 150°C case temperature at the rate of 0.32 W/°C.
3. $V_{CE} = 20$ V, $I_C = 1$ A, $P_W = 10$ ms, duty cycle $\leq 2\%$.

TIPP115, TIPP116, TIPP117

PNP SILICON POWER DARLINGTONS

electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10 \text{ mA}$ (see Note 4)	$I_B = 0$	TIPP115	-60			V
				TIPP116	-80			
				TIPP117	-100			
I_{CEO}	Collector-emitter cut-off current		$V_{BE} = 0$	TIPP115			-2	mA
				TIPP116			-2	
				TIPP117			-2	
I_{CBO}	Collector-base cut-off current		$I_B = 0$	TIPP115			-1	mA
				TIPP116			-1	
				TIPP117			-1	
I_{EBO}	Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-2	mA
h_{FE}	Forward current transfer ratio	$V_{CE} = -4 \text{ V}$	$I_C = -1 \text{ A}$	(see Notes 4 and 5)	1000			
		$V_{CE} = -4 \text{ V}$	$I_C = -2 \text{ A}$		500			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = -8 \text{ mA}$	$I_C = -2 \text{ A}$	(see Notes 4 and 5)			-2.5	V
V_{BE}	Base-emitter voltage	$V_{CE} = -4 \text{ V}$	$I_C = -2 \text{ A}$	(see Notes 4 and 5)			-2.8	V
V_{EC}	Parallel diode forward voltage	$I_E = -4 \text{ A}$	$I_B = 0$	(see Notes 4 and 5)			-3.5	V

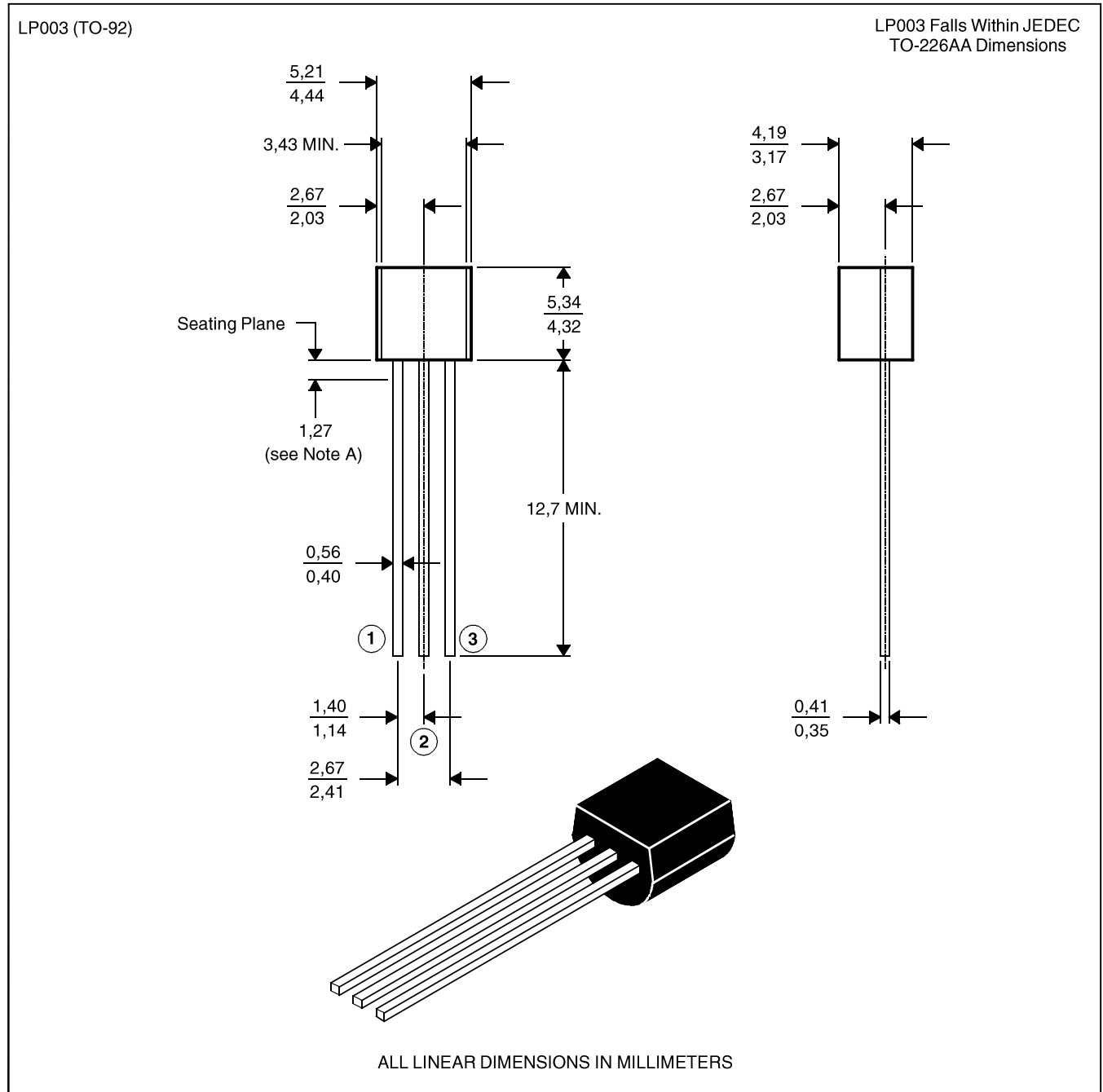
- NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.
5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

MECHANICAL DATA

LP003 (TO-92)

3-pin cylindrical plastic package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: Lead dimensions are not controlled in this area.

TIPP115, TIPP116, TIPP117
PNP SILICON POWER DARLINGTONS

MECHANICAL DATA

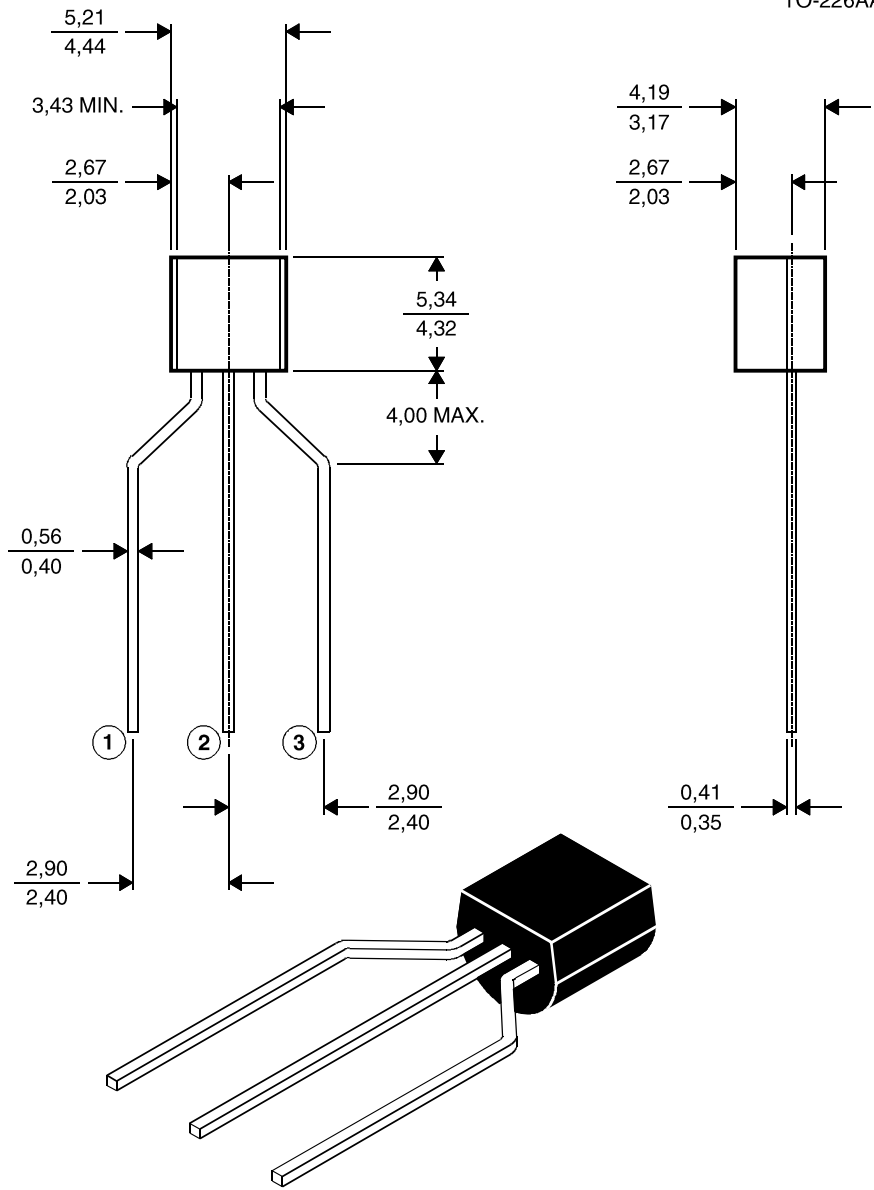
LP003 (TO-92)

3-pin cylindrical plastic package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.

LP003 (TO-92) - Formed Leads Version

LP003 Falls Within JEDEC
TO-226AA Dimensions



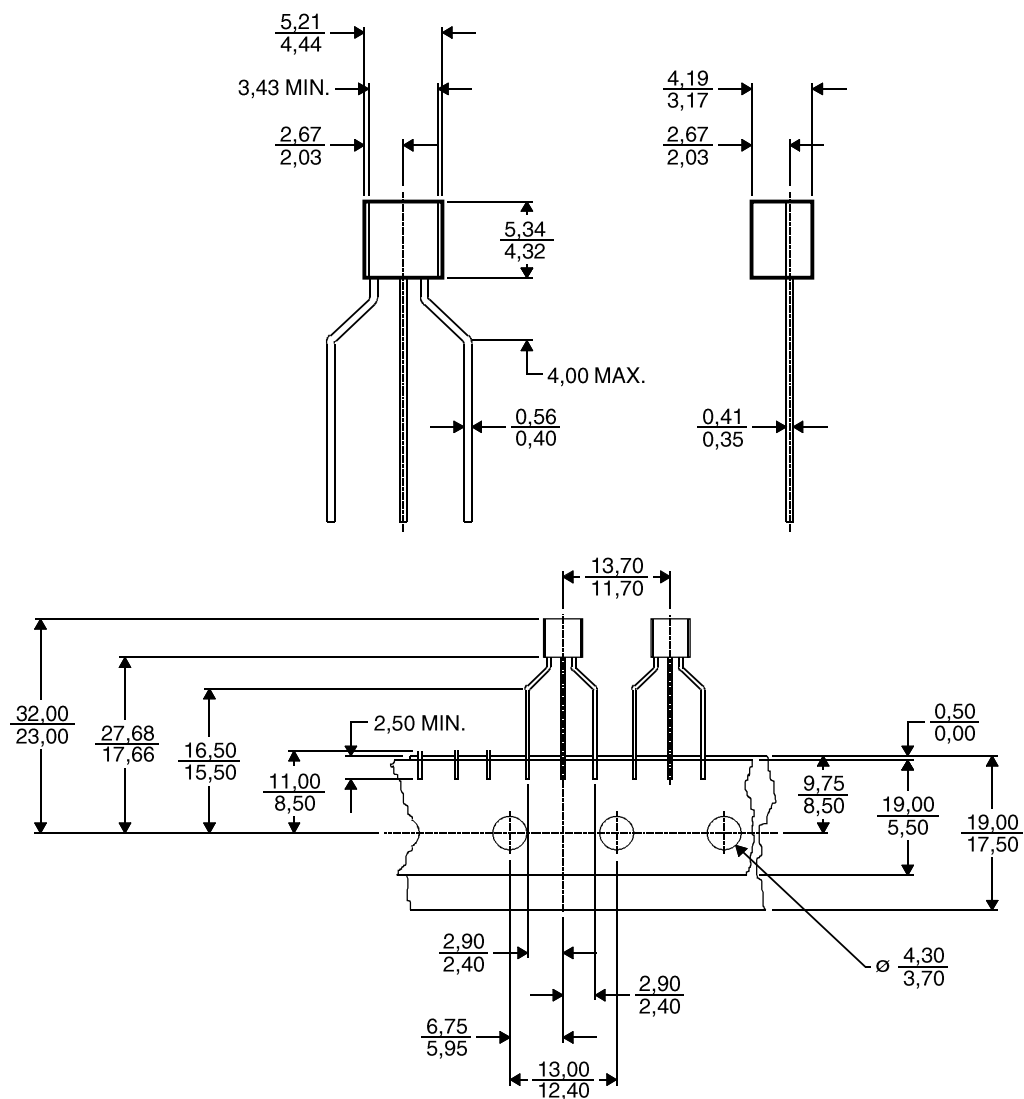
ALL LINEAR DIMENSIONS IN MILLIMETERS

MECHANICAL DATA

LPR

tape dimension s

LP Package (TO-92) Tape (Formed Lead Version)



ALL LINEAR DIMENSIONS IN MILLIMETERS